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INFORMATION DISCLOSURE	Application Number	09/896,797			
STATEMENT BY APPLICANT	Filing Date	6/29/2001			
Date Submitted: October 22, 2009	First Named Inventor	John Trezza			
Date Submitted. October 22, 2009	Art Unit	2613	•		
(use as many sheets as necessary	Examiner Name	Agustin Bello			
Sheet 1 of 1	Attorney Docket Number	088245-4667			

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Examin	Cite	Document Number	Publication Date	Name of Patentee or Applicant of	Pages, Columns, Lines, Where Relevant
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Examiner Signature	/Agustin Bello/ (06/30/2010)	Date Considered

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

FORM PTO-1449 INFORMATION DISCLOSURE CITATION				Attorney Do 4024-4008 Applicant: John Trezza Filing Date:	<del>,</del>		Serial No.: 09/896,797	nit.
	TRADENT		June 29, 2001 2872			Group Art U 2872	Unit:	
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